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JAPANESE PATENT OFFICE

PATENT ABSTRACTS OF JAPAN

(11) Publication number: 08255791 A

(43) Date of publication of application: 01 . 10 . 96

(51) Int. Cl

H01L 21/316**H01L 21/304****H01L 21/324****H01L 21/768**

(21) Application number: 07057849

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(22) Date of filing: 17 . 03 . 95

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KOYANAGI KENICHI(54) FORMATION OF INTERLAYER INSULATING
FILM OF SEMICONDUCTOR DEVICE

(57) Abstract:

PURPOSE: To form an interlayer insulating film covering a MOS transistor of a titanium salicide structure by suppressing degradation of transistor characteristics and coagulation of titanium silicide film.

CONSTITUTION: A silicon dioxide film 21 is formed by the LPCVD process, a PSG film 31 is formed by the APCVD process using ozone, TEOS, etc., as raw materials, these films are heat-treated in a 750°C nitrogen atmosphere, and a silicon dioxide film 41 is formed by the ECR-PECVD process, and the surface of this silicon dioxide film 41 is polished by the CMP process.

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